

E-Series Automotive 650 V, 30 A Silicon Carbide Schottky Diode

Description

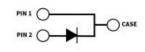
With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.











Part Number	Package	Marking	
E6D30065G	TO-263-2	E6D30065G	

Features

- Low Forward Voltage (V_F) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Automotive Qualified (AEC Q101) and PPAP Capable

Applications

- Interleaved or Bridgless PFC
- DC/DC On Board Battery Chargers
- Boost for PFC & DC-DC Stages
- AC/DC On Board Chargers
- PFC Output Rectification

Maximum Ratings ($T_c = 25^{\circ}$ C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Notes
Repetitive Peak Reverse Voltage	V _{RRM}	650			
Surge Peak Reverse Voltage	V _{RSM}	650	V		
DC Blocking Voltage	V _{DC}	650			
		95		T _c = 25 °C	
Continuous Forward Current	I _F	49		T _c = 125 °C	Fig. 3
		31	A	T _c = 150 °C	
Repetitive Peak Forward Surge		111		T _C = 25 °C, t _p = 10 ms, Half Sine Wave	
Current	FRM	64		$T_c = 110 ^{\circ}\text{C}, t_p = 10 \text{ms}, \text{Half Sine Wave}$	
Non-Repetitive Forward Surge		194		T _c = 25 °C, t _p = 10 ms, Half Sine Wave	
Current	FSM	164	A	$T_c = 110 ^{\circ}\text{C}, t_p = 10 \text{ms}, \text{Half Sine Wave}$	
2 2	_	306		T _c = 25 °C	
Power Dissipation	P _{tot}	133	W	T _c = 110 °C	Fig. 4
*20	63.11	188		$T_c = 25 {}^{\circ}\text{C}, t_p = 10 \text{ms}$	
i²t value	∫i²dt	135	A ² s	$T_c = 110 {}^{\circ}\text{C}, t_p = 10 \text{ms}$	

Electrical Characteristics

Parameter	Symbol	Тур.	Max.	Unit	Test Conditions	Notes
Famous ad Malda as		1.35	1.5		$I_F = 30 \text{ A}, T_j = 25 ^{\circ}\text{C}$	F:_ 1
Forward Voltage	V _F	1.5	1.6	V	$I_F = 30 \text{ A}, T_j = 175 \text{ °C}$	Fig. 1
Decrees Comment		10	100		$V_R = 650 \text{ V}, T_j = 25 \text{ °C}$	Fig. 2
Reverse Current	I _R	22	350	μΑ	$V_R = 650 \text{ V}, T_j = 175 \text{ °C}$	
Total Capacitive Charge	Q _c	98		nC	$V_R = 400 \text{ V}, T_j = 25 \text{ °C}$	Fig. 5
		1841			$V_R = 0 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Total Capacitance	c	187		pF	$V_R = 200 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	Fig. 6
		143			$V_R = 400 \text{ V}, T_j = 25 \text{ °C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	E _c	14.6		μJ	V _R = 400 V	Fig. 7

Notes:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

Parameter	Symbol	Value	Unit	Notes
Thermal Resistance, Junction to Case (Typical)	R _{θ, JC (TYP)}	0.38	°C/W	
Thermal Resistance, Junction to Case (Max)	R _{0, JC (MAX)}	0.49	°C/W	
Junction Temperature	T _j	-55 to +175		
Case & Storage Temperature	T _c	-55 to +175	°C	

Typical Performance

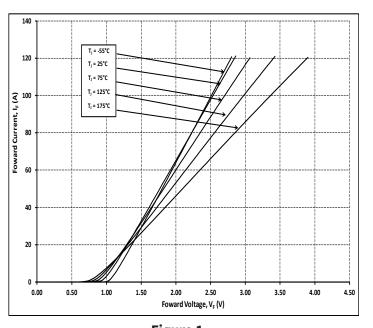
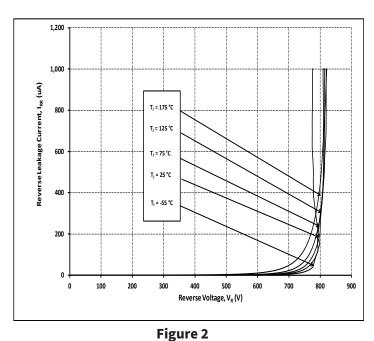


Figure 1Forward Characteristics



Reverse Characteristics

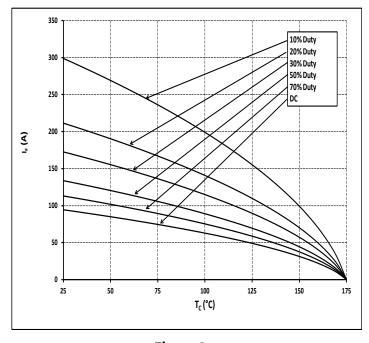


Figure 3Current Derating

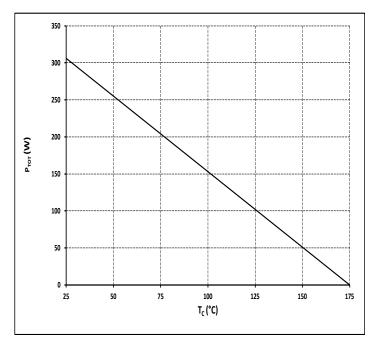


Figure 4Power Derating

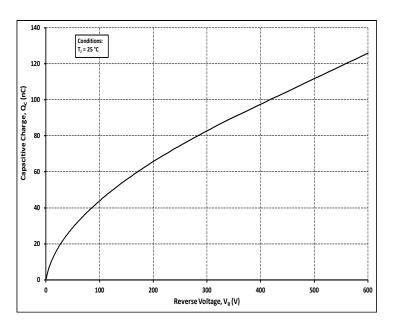


Figure 5 Total Capacitance vs. Reverse Voltage

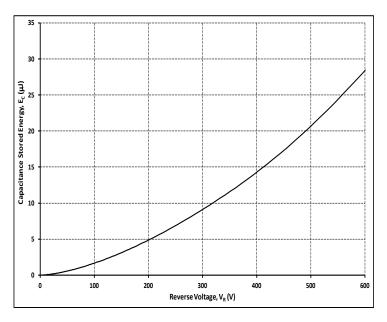


Figure 7 Capacitance Stored Energy

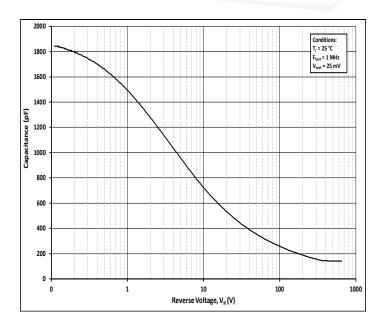


Figure 6 Capacitace vs. Reverse Voltage

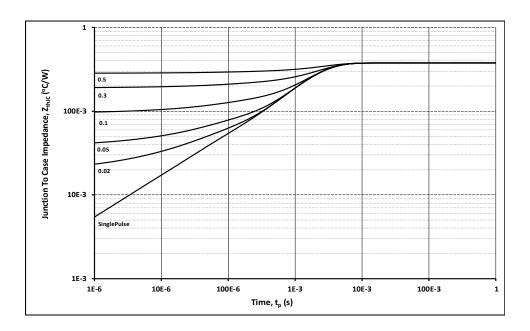
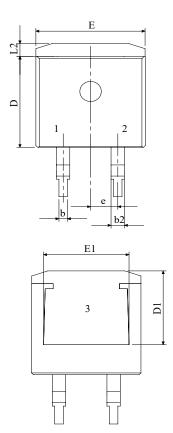


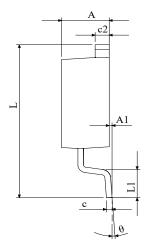
Figure 8Transient Thermal Impedance

Package Dimensions & Pin-Out

Package: TO-263-2



SYMBOL	MIN (mm)	MAX (mm)	
A	4.32	4.57	
A1		0.25	
ь	0.71	0.94	
b2	1.15	1.40	
c	0.356	0.635	
c2	1.22	1.40	
D	8.89	9.40	
D1	6.48	6.88	
E	10.04	10.28	
E1	7.535	8.425	
e	2.54		
L	14.73	15.75	
L1	2.29	2.79	
L2	1.15	1.39	
θ	0°	8°	



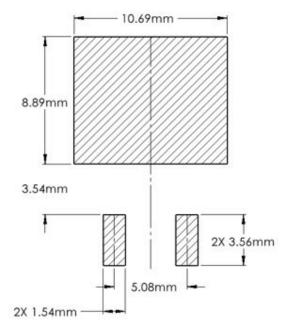
1	CATHODE
2	ANODE
3	CATHODE

NOTE

- 1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.
- 2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
- 3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
- 4. PACKAGE BURR FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS

Recommended Solder Pad Layout

Primary dimensions shown in mm.



Product Ordering Information

Order Number	Packing Type	
E6D30065G-TR	Tape & Reel	
E6D30065G	Tube	

Revision History

Document Version	Date of Release	Description of Changes
1	February 2024	Initial Release

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